



DMN2005K

N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Features

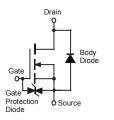
- Low On-Resistance
- Very Low Gate Threshold Voltage, 0.9V Max.
- · Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- ESD Protected Gate

Mechanical Data

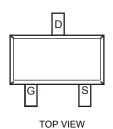
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Copper leadframe.
 Solderable per MIL-STD-202, Method 208 63
- Ordering & Date Code Information: See Below
- Weight: 0.008 grams (approximate)











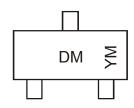
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2005K-7	SOT23	3000/Tape & Reel

Notes:

- $1.\ No\ purposely\ added\ lead.\ Fully\ EU\ Directive\ 2002/95/EC\ (RoHS)\ \&\ 2011/65/EU\ (RoHS\ 2)\ compliant.$
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



DM = Product Type Marking Code YM = Date Code Marking Y = Year ex: T = 2006 M = Month ex: 9 = September

Date Code Key

Year	2006	2007	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017	2018	2019	2020
Code	T	C	٧	W	Х	Υ	Ζ	Α	В	С	D	Е	F	G	Н
Month	Jan	Feb) N	/lar	Apr	May	Jur	1	Jul	Aug	Sep	Oc	t	Nov	Dec
Code		_		_					_	•		_			_



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		V_{DSS}	20	V
Gate-Source Voltage		V_{GSS}	±10	V
Drain Current per element (Note 5)	Continuous Pulsed (Note 6)	I _D	300 600	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

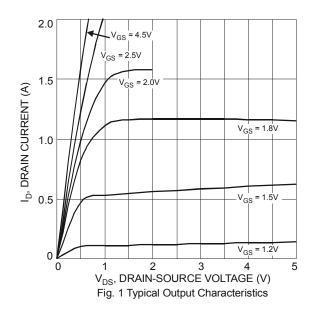
Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_{D}	350	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	357	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-65 to +150	°C

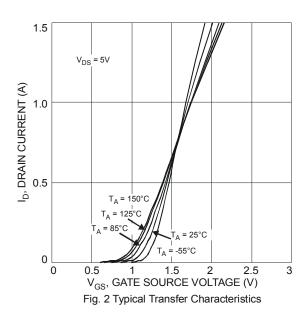
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	20	_	_	V	$V_{GS} = 0V, I_D = 100\mu A$
Zero Gate Voltage Drain Current	I _{DSS}	_	_	10	μA	V _{DS} = 17V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	_	_	±5	μΑ	$V_{GS} = \pm 8V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(th)}	0.53	_	0.9	V	$V_{DS} = V_{GS}, I_{D} = 100 \mu A$
Static Drain-Source On-Resistance	R _{DS(ON)}	_	0.55 0.4	3.5 1.7	Ω	V_{GS} = 1.8V, I_{D} = 200mA V_{GS} = 2.7V, I_{D} = 200mA
Forward Transfer Admittance	Y _{fs}	40		_	mS	$V_{DS} = 3V, I_{D} = 10mA$

Notes:

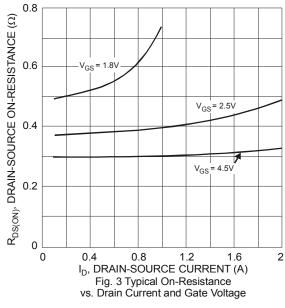
- 5. Device mounted on FR-4 PCB.
- 6. Pulse width ≤10μS, Duty Cycle ≤1%.
- 7. Short duration pulse test used to minimize self-heating effect.

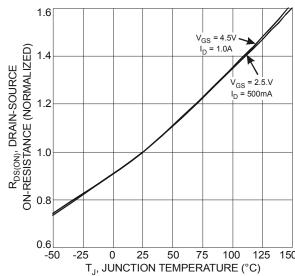












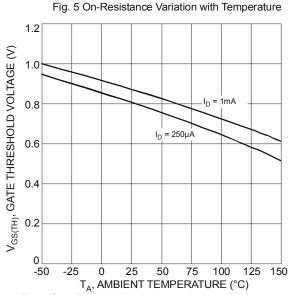


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

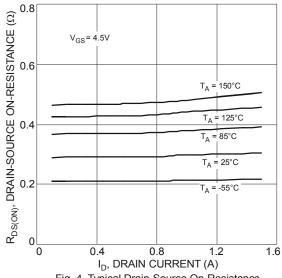


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

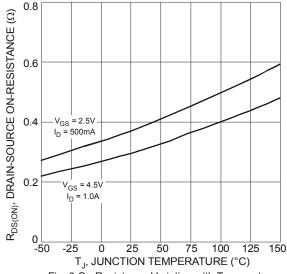


Fig. 6 On-Resistance Variation with Temperature

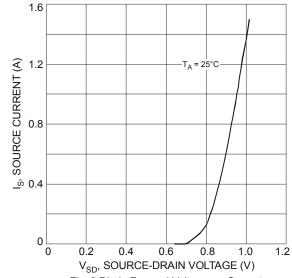
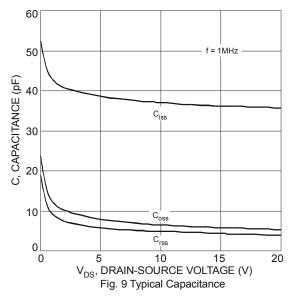


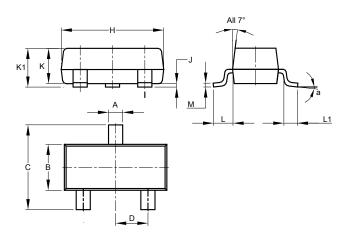
Fig. 8 Diode Forward Voltage vs. Current





Package Outline Dimensions

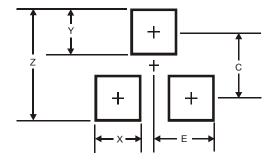
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23								
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
C	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
H	2.80	3.00	2.90					
7	0.013	0.10	0.05					
K	0.890	1.00	0.975					
K1	0.903	1.10	1.025					
L	0.45	0.61	0.55					
L1	0.25	0.55	0.40					
М	0.085	0.150	0.110					
а	8°							
All Dimensions in mm								

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Υ	0.9
С	2.0
E	1.35



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